



迈拓电子  
MAITUO ELECTRONIC

## BAT54W1 SCHOTTKY BARRIER DIODE

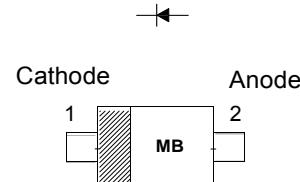
### Features

- Low forward voltage

### Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits

Marking Code: "MB"



SOD-123

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Forward Current	$I_F$	200	mA
Repetitive Peak Forward Current	$I_{FRM}$	300	mA
Peak Forward Surge Current ( $t_p = 10 \text{ ms}$ )	$I_{FSM}$	600	mA
Power Dissipation	$P_D$	230	mW
Thermal Resistance from Junction Ambient	$R_{thJA}$	500	K/W
Junction Temperature	$T_J$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 0.1 \text{ mA}$ at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 30 \text{ mA}$ at $I_F = 100 \text{ mA}$	$V_F$	240 320 400 500 800	mV
Reverse Current at $V_R = 25 \text{ V}$	$I_R$	2	$\mu\text{A}$
Total Capacitance at $V_R = 1 \text{ V}$ , $f = 1 \text{ MHz}$	$C_T$	10	pF
Reverse Recovery Time at $I_F = 10 \text{ mA}$ , $V_R = 6 \text{ V}$ , $I_R = 10 \text{ mA}$ , $R_L = 100 \Omega$	$t_{rr}$	6	ns



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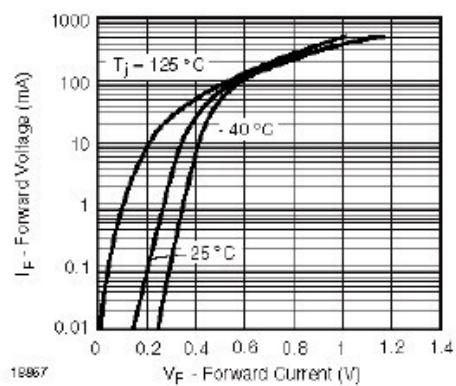


Figure 1. Typical Forward Voltage Forward Current at Various Temperatures

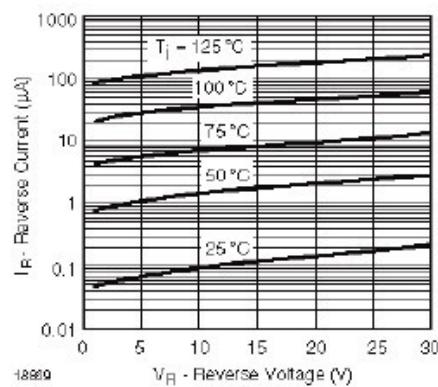


Figure 3. Typical Variation of Reverse Current at Various Temperatures

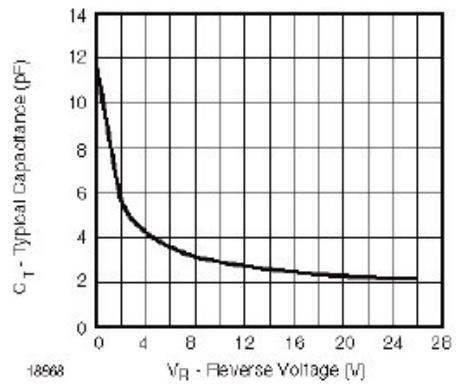


Figure 2. Typical Capacitance  $\text{C}_T$  vs. Reverse Applied Voltage  $V_R$

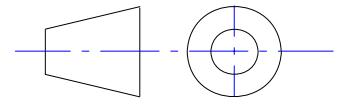
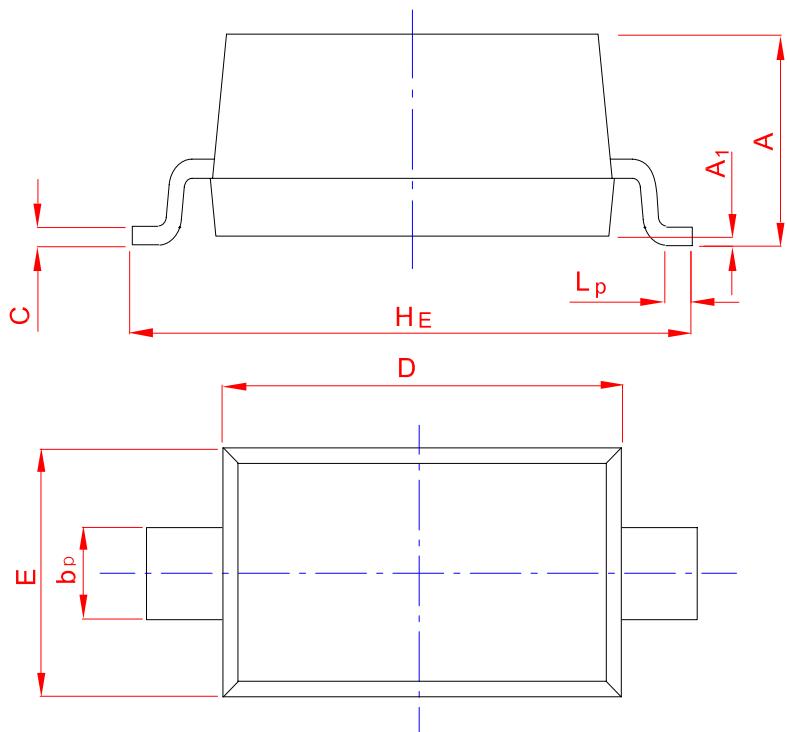


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## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

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UNIT	A	$b_p$	C	D	E	$H_E$	A <sub>1</sub>	L <sub>p</sub>
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20